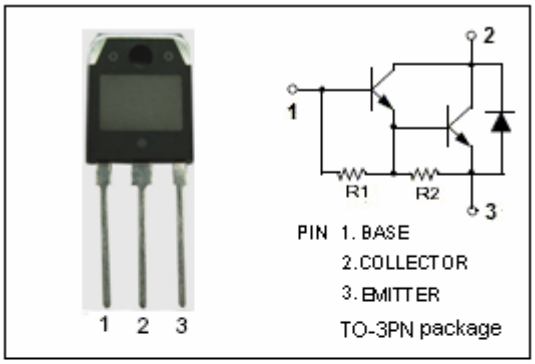
Silicon NPN Darlington Power Transistor BU826A

DESCRIPTION

・Collector-Emitter Sustaining Voltage-
: $V_{CEO(SUS)}$= 400V(Min)
・High Switching Speed



APPLICATIONS

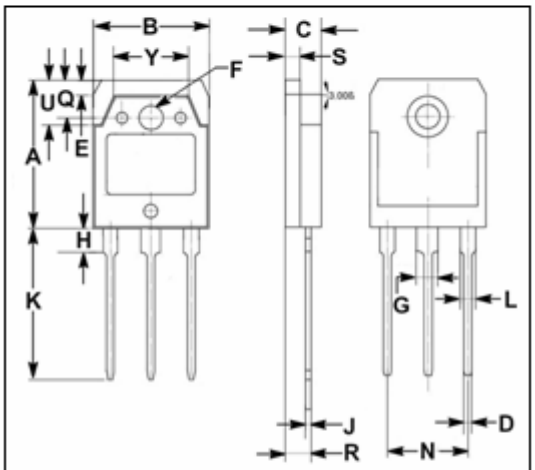
Designed for line operated switchmode applications such as:
・Switching regulators
・Inverters
・Solenoid and relay drivers

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CES}	Collector-Emitter Voltage(V_{BE}= 0)	1000	V
V_{CEO}	Collector-Emitter Voltage	400	V
V_{EBO}	Emitter-Base Voltage	8	V
I_C	Collector Current-Continuous	6	A
I_{CM}	Collector Current-Peak	8	A
I_B	Base Current	0.5	A
P_C	Collector Power Dissipation @ T_C=25℃	125	W
T_J	Junction Temperature	150	℃
T_{stg}	Storage Temperature Range	-65~150	℃

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j\text{-}c}$	Thermal Resistance, Junction to Case	1.0	℃/W



DIM	mm MIN	MAX
A	19.90	20.10
B	15.50	15.70
C	4.70	4.90
D	0.90	1.10
E	1.90	2.10
F	3.40	3.60
G	2.90	3.10
H	3.20	3.40
J	0.595	0.605
K	20.50	20.70
L	1.90	2.10
N	10.89	10.91
Q	4.90	5.10
R	3.35	3.45
S	1.995	2.005
U	5.90	6.10
Y	9.90	10.10

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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CEO(SUS)}$	Collector-Emitter Sustaining Voltage	I_C= 100mA ;I_B= 0,L= 25mH	400			V
$V_{CE(sat)-1}$	Collector-Emitter Saturation Voltage	I_C= 2.5A; I_B= 55mA			2.0	V
$V_{CE(sat)-2}$	Collector-Emitter Saturation Voltage	I_C= 4A; I_B= 0.2A			2.5	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	I_C= 2.5A; I_B= 55mA			2.2	V
I_{CES}	Collector Cutoff Current	V_{CE}= RatedV_{CES}; R_{BE}= 0 V_{CE}= RatedV_{CES}; R_{BE}= 0,T_C= 125℃			1.0 2.0	mA
I_{EBO}	Emitter Cutoff Current	V_{EB}= 8V; I_C= 0			150	mA